





Circuit

IGBT Modules

 V_{CES} 1200V Ic 100A

Applications

- · AC and DC motor control
- · PFC
- · SMPS
- · Brake switch

Features

- Low V_{CE(sat)} with Trench Field-stop technology
 V_{CE(sat)} with positive temperature coefficient
 Small temperature coefficient

- Low inductance
- · Isolated copper baseplate using DBC technology
- · SOT-227 package

Absolute Maximum Ratings

Parameter	Symbol	Conditions	Value	Unit
Collector-Emitter Voltage	V _{CES}	V _{GE} =0V, I _C =1mA, T _{vj} =25 °C	1200	V
Continuous Collector Current	Ic	T _C =100℃	100	А
Peak Collector Current	Icrm	t _p =1ms	200	Α
Gate-Emitter Voltage	V _{GES}	T _{vj} =25℃	±20	V
Total Power Dissipation (IGBT-inverter)	P _{tot}	T _c =25°C T _{vjmax} =175°C	535	W



MG100UZ12TLGJ ROHS COMPLIANT

IGBT Characteristics

Parameter	Symbol	Conditions	Value			Unit
			Min.	Тур.	Max.	
Gate-Emitter Threshold Voltage	$V_{\text{GE(th)}}$	V_{GE} = V_{CE} , I_{C} = 4 mA, T_{vj} = 25 °C	5.0	5.8	6.5	V
Collector-Emitter Cut-off Current	I _{CES}	V _{CE} =1200V,V _{GE} =0V, T _{vj} =25°C			1.0	mA
		V _{CE} =1200V,V _{GE} =0V, T _{vj} =125°C			5.0	mA
	V _{CE(sat)}	I _C =100A,V _{GE} =15V, T _{vj} =25°C		1.85	2.25	V
Collector-Emitter Saturation Voltage		I _C =100A,V _{GE} =15V, T _{vj} =125°C		2.10		V
Cataration voltage		I _C =100A,V _{GE} =15V, T _{vj} =150°C		2.20		V
Gate Charge	Q_{G}			0.68		uC
Input Capacitance	Cies	V _{CE} =25V, V _{GE} =0V, f=1MHz, T _{vj} =25°C		8.8		nF
Reverse Transfer Capacitance	C _{res}			0.27		nF
Internal Gate Resistance	R _{gint}			7.5		Ω
Turn-on Delay Time	t _{d(on)}			129		ns
Rise Time	t _r	1 4004		40		ns
Turn-off Delay Time	$t_{d(off)}$	I_{C} =100A V_{CE} =600V V_{GE} =±15V R_{G} =1.5Ω T_{vj} =25°C		232		ns
Fall Time	t _f			176		ns
Energy Dissipation During Turn-on Time	Eon			6.2		mJ
Energy Dissipation During Turn-off Time	E _{off}			6.7		mJ
Turn-on Delay Time	t _{d(on)}	- I _C =100A V _{CE} =600V V _{GE} =±15V R _G =1.5Ω T _{vj} =150°C		105		ns
Rise Time	t _r			46		ns
Turn-off Delay Time	t _{d(off)}			260		ns
Fall Time	t _f			309		ns
Energy Dissipation During Turn-on Time	Eon			10.7		mJ
Energy Dissipation During Turn-off Time	E _{off}			10.3		mJ
SC Data	Isc	$t_p \le 10us, V_{GE} = 15V,$ $T_{vj} = 150 ^{\circ}\text{C}, V_{CC} = 600V,$ $V_{CEM} \le 1200V$		400		A

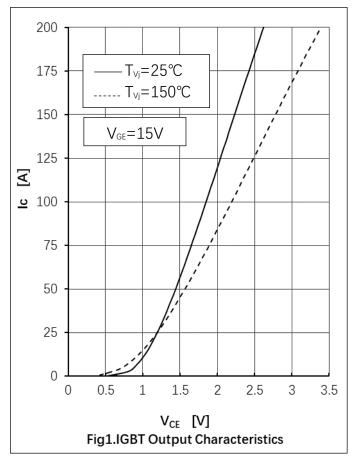


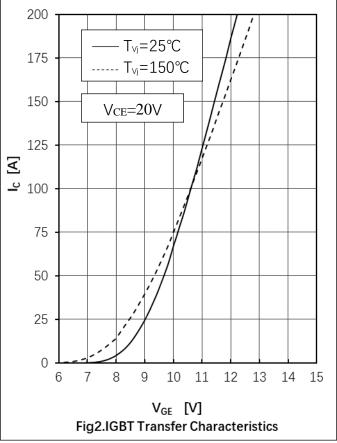
MG100UZ12TLGJ ROHS COMPLIANT

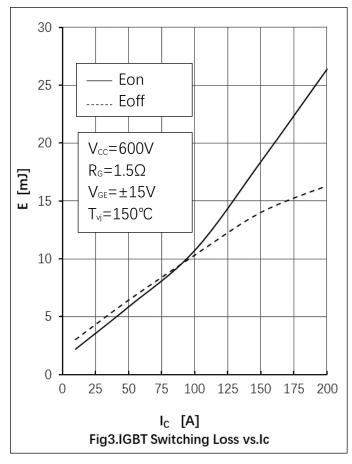
● Module Characteristics T_C=25°C unless otherwise specified

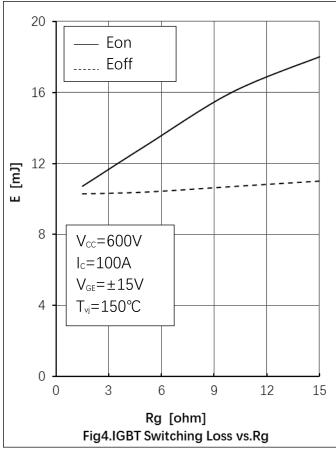
Parameter	Symbol	Conditions	Value			
			Min.	Тур.	Max.	Unit
Isolation Voltage	V _{isol}	t=1min,f=50Hz	2500			V
Maximum Junction Temperature	T_{jmax}				175	$^{\circ}$
Operating Junction Temperature	T _{vj op}		-40		150	$^{\circ}$
Storage Temperature	T _{stg}		-40		125	$^{\circ}$
Junction to Case	$R_{\theta jc}$	per IGBT			0.28	K/W
Case to Sink	R _{θcs}	Conductive grease applied		0.15		K/W
Module Electrodes Torque	Mt	Recommended(M4)	0.7	1.0	1.5	N·m
Module to Sink Torque	Ms	Recommended(M4)	0.7	1.0	1.5	N·m
Weight of Module	G			32		g



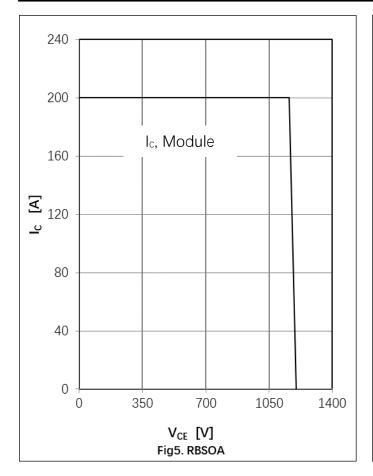


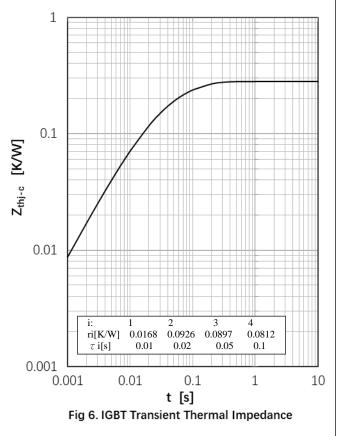






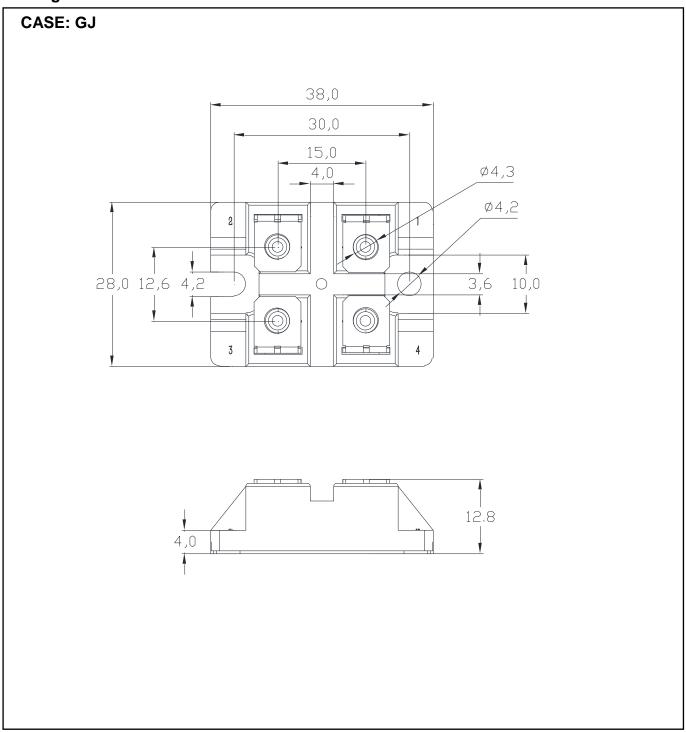








Package Outline Information







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IGBTs is the device which is sensitive to the static electricity, it is necessary to protect the device from being damaged by the static electricity when using it.

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